

Ultra Low ON-Resistance, Low Voltage, Dual, SPDT Analog Switch

Features

- Wide Power Supply Range: 1.65V to 5.5V
- Low On-Resistance:
 $R_{ON(NC)} = 0.3 \Omega$ (VCC=5V)
 $R_{ON(NO)} = 0.3 \Omega$ (VCC=5V)
- Low On-Resistance Flatness:
 $R_{FLAT(NC)} = 0.08 \Omega$ (VCC=5V)
 $R_{FLAT(NO)} = 0.08 \Omega$ (VCC=5V)
- -3dB Bandwidth: 33MHz
- Rail-to-Rail Signal Range
- High Off-Isolation: -66dB (f=100 kHz)
- Crosstalk Rejection: -74dB
- Low Total Harmonic Distortion: 0.035%
- Available in MSOP10 package

Applications

- Wireless Handsets
- Portable Electronic Devices
- Relay Replacement
- PDAs
- Audio & Video Signal Routing
- PCMCIA Cards
- Computer Peripherals
- Modems

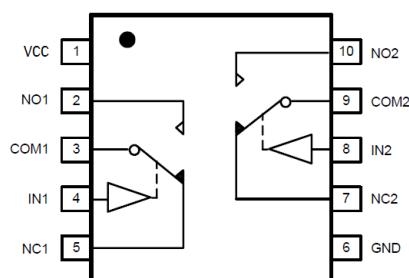
Function Table

IN _x	Function
0	NC _x Connected to COM _x
1	NO _x Connected to COM _x

Description

The BL1555 is a Dual Wide-Bandwidth, fast single-pole double-throw (SPDT) CMOS switch featuring an On-Resistance of 0.3 ohm at V_{DD}=5V and wide power supply range from 1.65V to 5.5V. It can be used as an analog switch or as a low-delay bus switch. Break-before-make function for both parts eliminates signal disruption during switching from preventing both switches being enabled simultaneously.

Pin Configuration



Pin Description

Pin Name	Type	Description
VCC	PWR	Power Supply
GND	Ground	Ground
COMx	Input/Output	Data Port
NCx	Input/Output	Data Port
NOx	Input/Output	Data Port
INx	Input	Logic Control Signal

** X = 1 or 2

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Units
DC Supply Voltage	V _{CC}	-0.5	6	V
DC Switch Voltage	V _{NCX} / V _{NOX} / V _{COMX}	-0.5	V _{SUP} + 0.3	V
DC Input Voltage	V _{INX}	-0.5	6	V
Continuous Current	I _(NCX/NOX/COMX)	-250	+250	mA
Peak Current ⁽¹⁾	I _{PEAK(NCX/NOX/COMX)}	-350	+350	mA
Storage Temperature Range	T _{STG}	-65	150	°C

Notes:

- (1) Pulsed at 1ms, 50% duty circle
- (2) Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device.
These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- (3) Control input(V_{INX}) must be held HIGH or LOW, and mustn't be floated.

RECOMMENDED OPERATING CONDITIONS

DC Supply Voltage (V_{CC}) 1.65V to 5.5V
 Switch Input Voltage (V_S) 0V to V_{CC}
 Control Input Voltage (V_{IN}) 0V to V_{CC}
 Operation Temperature (TA) -40°C to +125°C

DC ELECTRICAL CHARACTERISTICS

(VCC=5V, TA=+25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Guaranteed Limit			Unit
			Min.	Typ.	Max.	
Analog Switch						
Analog Signal Range	V _{NOX} /V _{NCX} / V _{COMX}		0		V _{CC}	V
NC On-Resistance	R _{ON(NC)}	V _{CC} = 5V; I _{COM} = 100mA ; V _{NC} = 0 to V _{CC}		0.3	0.6	Ω
NO On-Resistance	R _{ON(NO)}	V _{CC} = 5V; I _{COM} = 100mA ; V _{NO} = 0 to V _{CC}		0.3	0.6	Ω
NC On-Resistance Flatness ⁽¹⁾	R _{FLAT(NC)}	V _{CC} = 5V; I _{COM} = 100mA ; V _{NC} = 0 to V _{CC}		0.08	0.2	Ω
NO On-Resistance Flatness ⁽¹⁾	R _{FLAT(NO)}	V _{CC} = 5V; I _{COM} = 100mA ; V _{NO} = 0 to V _{CC}		0.08	0.2	Ω
On-Resistance Match Between Channels ⁽²⁾	△R _{ON}	V _{CC} = 5V; I _{COM} = 100mA ; V _{NC} /V _{NO} =1.5		0.03	0.09	Ω
NC or NO Off Leakage Current	I _{OFF(NC)} or I _{OFF(NO)}	V _{CC} = 5V; V _{NO} or V _{NC} = 3V, 0.3V; V _{COM} = 0.3V, 3 V		4		nA
COM On Leakage Current	I _{ON(COM)}	V _{CC} = 5V; V _{NO} or V _{NC} = 3V, 0.3V; V _{COM} = 0.3V, 3 V or floating		4		nA
Digital I/O						
Input Voltage High	V _{IH}	Minimum High Level Input Voltage	1.8			V
Input Voltage Low	V _{IL}	Maximum Low Level Input Voltage			0.6	V
Input Hysteresis	I _H	V _{CC} = 5V		200		mV
Input Leakage Current	I _{IN}	V _{IN} = 0 or V _{CC}	-1		1	uA

DC ELECTRICAL CHARACTERISTICS

(VCC=2.7V, TA=+25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Guaranteed Limit			Unit
			Min.	Typ.	Max.	
Analog Switch						
Analog Signal Range	V _{NOX} /V _{NCX} / V _{COMX}		0		V _{CC}	V
NC On-Resistance	R _{ON(NC)}	V _{CC} = 2.7V; I _{COM} = 100mA ; V _{NC} = 0 to V _{CC}		0.6	1.1	Ω
NO On-Resistance	R _{ON(NO)}	V _{CC} = 2.7V; I _{COM} = 100mA ; V _{NO} = 0 to V _{CC}		0.6	1.1	Ω
NC On-Resistance Flatness ⁽¹⁾	R _{FLAT(NC)}	V _{CC} = 2.7V; I _{COM} = 100mA ; V _{NC} = 0 to V _{CC}		0.26	0.4	Ω

NO On-Resistance Flatness ⁽¹⁾	R _{FLAT(NO)}	V _{CC} = 2.7V; I _{COM} = 100mA ; V _{NO} = 0 to V _{CC}		0.26	0.4	Ω
On-Resistance Match Between Channels ⁽²⁾	△R _{ON}	V _{CC} = 2.7V; I _{COM} = 100mA ; V _{NC} /V _{NO} = 1.5		0.05	0.1	Ω
NC or NO Off Leakage Current	I _{OFF(NC)} or I _{OFF(NO)}	V _{CC} = 2.7V; V _{NO} or V _{NC} = 2.7V, 0.3V; V _{COM} = 0.3V, 2.7V		4		nA
COM On Leakage Current	I _{ON(COM)}	V _{CC} = 2.7V; V _{NO} or V _{NC} = 2.7V, 0.3V; V _{COM} = 0.3V, 2.7V or floating		4		nA
Digital I/O						
Input Voltage High	V _{IH}	Minimum High Level Input Voltage	1.3			V
Input Voltage Low	V _{IL}	Maximum Low Level Input Voltage			0.6	V
Input Hysteresis	I _H	V _{CC} = 2.7V		200		mV
Input Leakage Current	I _{IN}	V _{IN} = 0 or V _{CC}	-1		1	uA

Note:

- (1) Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal ranges.
- (2) $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$, between NC1 and NC2 or between NO1 and NO2.

DYNAMIC CHARACTERISTICS(V_{CC}=3.3V, TA=+25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Guaranteed Limit			Unit
			Min.	Typ.	Max.	
AC ELECTRICAL CHARACTERISTICS						
Turn-On Time	t _{ON}	V _{CC} = 5V; V _{NO} or V _{NC} = 1.5V, R _L = 50Ω; C _L = 35pF, Figure1		42		ns
		V _{CC} = 3.3; V _{NO} or V _{NC} = 1.5V, R _L = 50Ω; C _L = 35pF, Figure1		43		
Turn-Off Time	t _{OFF}	V _{CC} = 5V; V _{NO} or V _{NC} = 1.5V, R _L = 50Ω; C _L = 35pF, Figure1		25		ns
		V _{CC} = 3.3; V _{NO} or V _{NC} = 1.5V, R _L = 50Ω; C _L = 35pF, Figure1		30		
Break-Before-Make Time	t _{BBA}	V _{CC} = 5V; V _{NO} or V _{NC} = 1.5V, R _L = 50Ω; C _L = 35pF, Figure2		22		ns
		V _{CC} = 3.3V; V _{NO} or V _{NC} = 1.5V, R _L = 50Ω; C _L = 35pF, Figure2		22		
NC OFF Capacitance	C _{OFF(NC)}	f = 1MHz, Figure6		82		pF
NO OFF Capacitance	C _{OFF(NO)}	f = 1MHz, Figure6		70		pF
NC ON Capacitance	C _{ON(NC)}	f = 1MHz, Figure7		255		pF
NO ON Capacitance	C _{ON(NO)}	f = 1MHz, Figure7		245		pF

ADDITIONAL APPLICATION CHARACTERISTICS

3dB Bandwidth	f _{3dB}	Figure8		33		MHz
Charge Injection	Q	V _{CC} =5V; V _{GEN} = 0V; R _{GEN} = 0Ω ; C _L = 1nF; Figure3		58		pC
		V _{CC} =3.3V; V _{GEN} = 0V; R _{GEN} = 0Ω ; C _L = 1nF; Figure3		45		
Off Isolation ⁽¹⁾	V _{Iso}	V _{CC} =5V; f = 100kHz; R _L = 50Ω ; C _L = 5pF; V _{COM} = 1 V _{RMS} ; Figure4		-66		dB
Crosstalk ⁽²⁾	V _{CT}	V _{CC} =5V; f = 100kHz; R _L = 50Ω ; C _L = 5pF; V _{COM} = 1 V _{RMS} ; Figure5		-74		dB
Total Harmonic Distortion	THD	V _{CC} = 5V; R _L = 32Ω ; V _{IN} = 2.8V _{P-P} ;		0.035		%
Supply						
Power Supply Range	V _{CC}		1.65		5.5	V
Maximum Quiescent Supply Current	I _{CC}	V _{CC} = 5.5V; V _{IN} = V _{CC} or 0			1	uA

Note:

(1) Off Channel Isolation = $20\log_{10} [(V_{NOINC})/V_{COM}]$

(2) Between any two switches

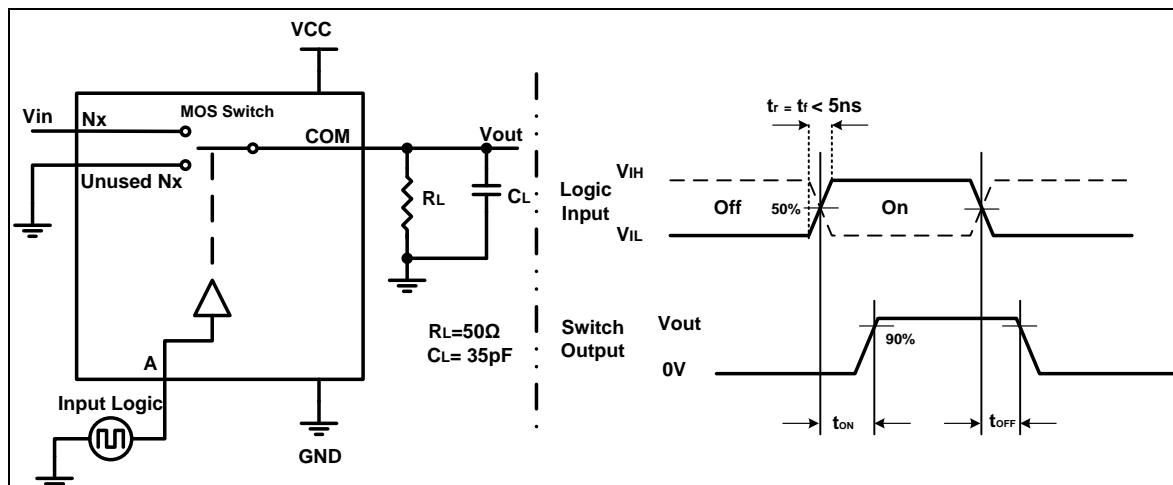
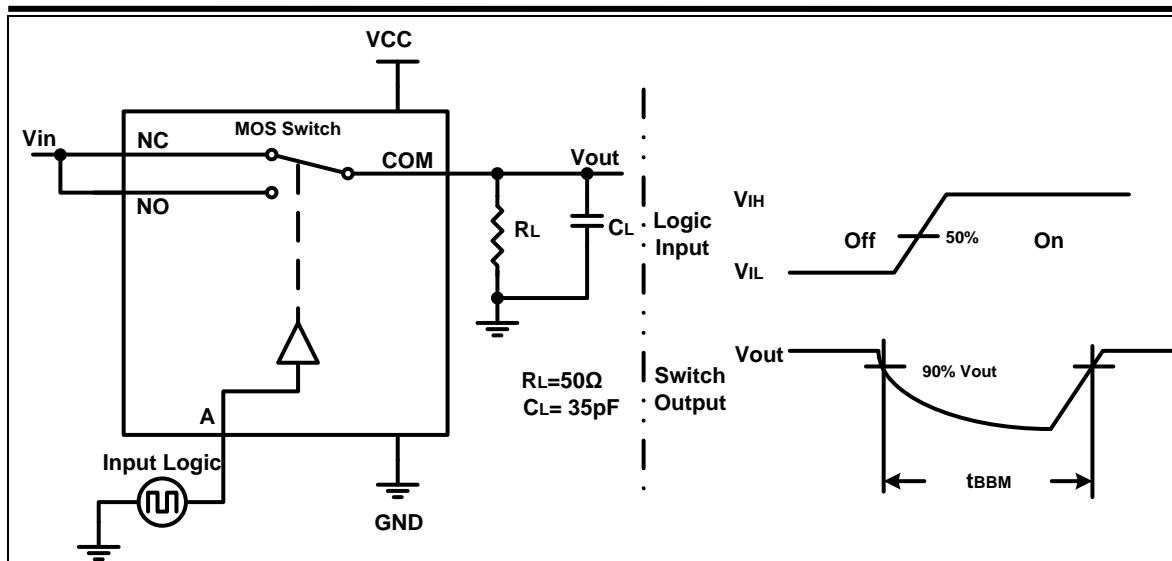
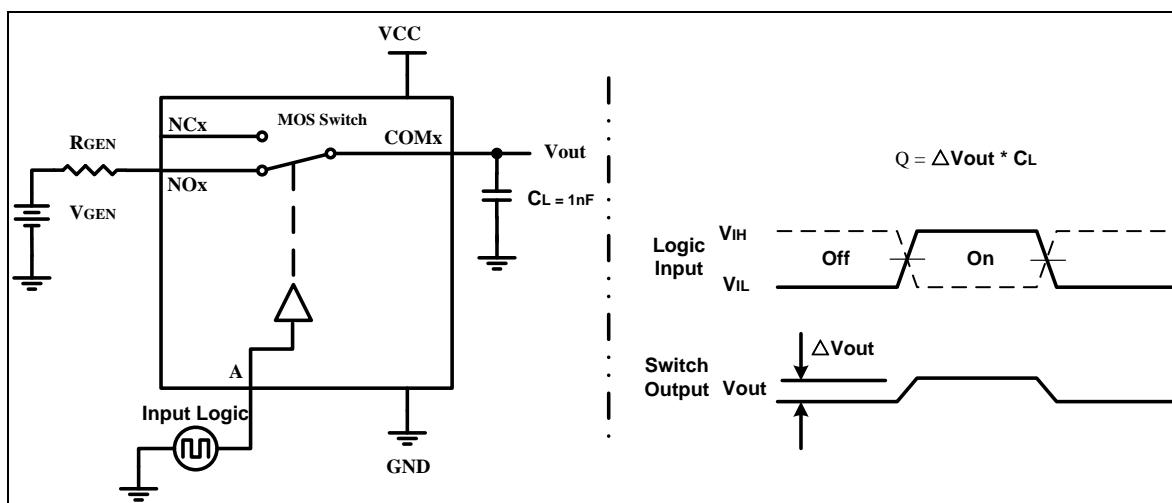
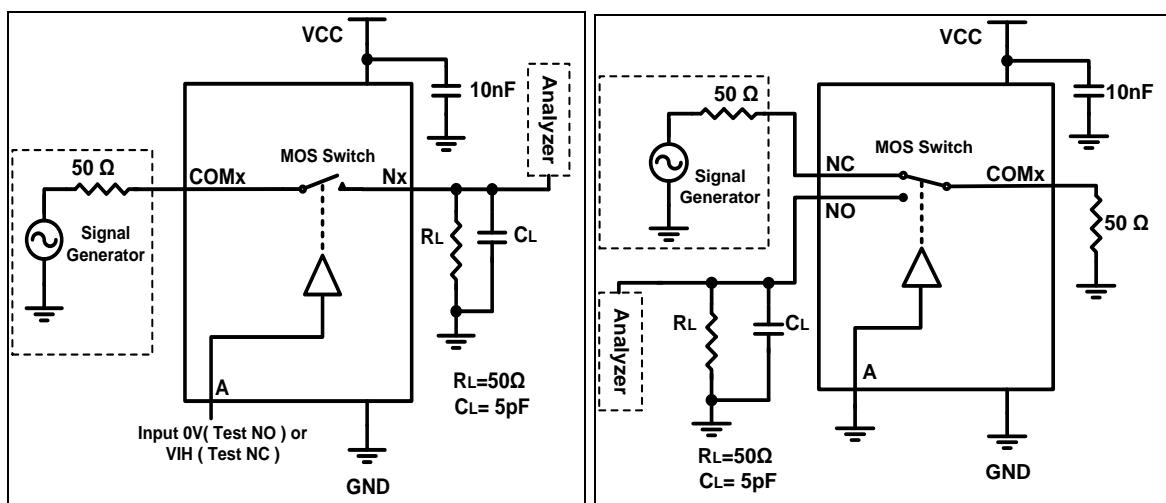
TEST SETUP CIRCUITS


Figure1. AC Test Circuit & Waveforms


Figure2. Break-Before-Make Time (t_{BBM})

Figure3. Charge Injection (Q)

Figure4. Off Isolation (V_{iso})
Figure5. Cross Talk (V_{ct})

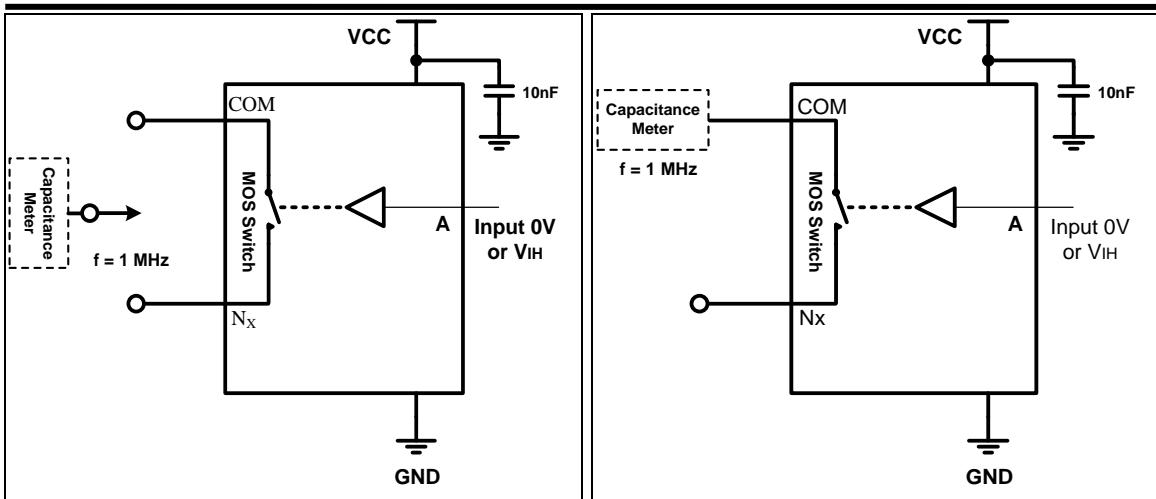


Figure6. Channel Off Capacitance($C_{OFF(Nx)}$) Figure7. Channel On Capacitance($C_{ON(Nx)}$)

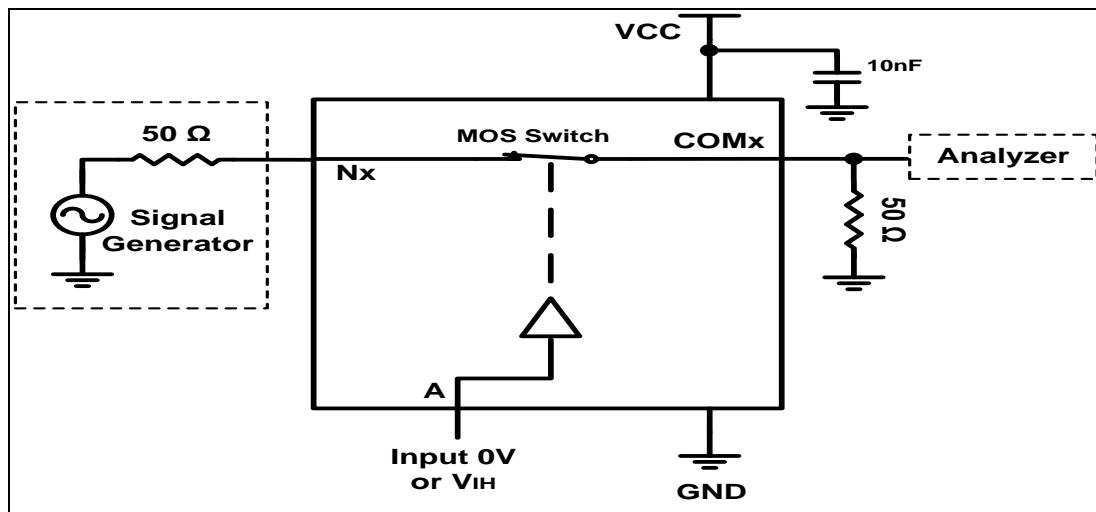


Figure8. -3dB Bandwidth (f_{3dB})

PACKAGE OUTLINE DIMENSIONS (MSOP10)
